

# Tetsuo Hatakeyama

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

20  
papers

343  
citations

8  
h-index

18  
g-index

20  
ext. papers

386  
ext. citations

2.2  
avg, IF

2.54  
L-index

#	Paper	IF	Citations
20	Dipole scattering at the interface: The origin of low mobility observed in SiC MOSFETs. <i>Journal of Applied Physics</i> , <b>2022</b> , 131, 145701	2.5	
19	Difference in electron mobility at 4H-SiC/SiO <sub>2</sub> interfaces with various crystal faces originating from effective-field-dependent scattering. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 042101	3.4	4
18	Ideal phonon-scattering-limited mobility in inversion channels of 4H-SiC(0001) MOSFETs with ultralow net doping concentrations. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 132102	3.4	12
17	Mobility-limiting Coulomb scattering in nitrided 4H-SiC inversion channel on 110 $\bar{1}$ 00 m-face and 112 $\bar{1}$ 00 a-face characterized by Hall effect measurements. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 132106	3.4	5
16	Impact of crystal faces of 4H-SiC in SiO <sub>2</sub> /4H-SiC structures on interface trap densities and mobilities. <i>Applied Physics Express</i> , <b>2019</b> , 12, 021003	2.4	12
15	Electrically detected-magnetic-resonance identifications of defects at 4H-SiC(0001)/SiO <sub>2</sub> interfaces with wet oxidation. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 151602	3.4	5
14	Surface defects generated by extrinsic origins on 4H-SiC epitaxial-wafers observed by scanning electron microscopy. <i>Microscopy (Oxford, England)</i> , <b>2017</b> , 66, 103-109	1.3	4
13	Pragmatic Approach to the Characterization of SiC/SiO <sub>2</sub> Interface Traps near the Conduction Band with Split C-V and Hall Measurements. <i>Materials Science Forum</i> , <b>2016</b> , 858, 477-480	0.4	3
12	Characterization of traps in SiC/SiO <sub>2</sub> interfaces close to the conduction band by deep-level transient spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 111301	1.4	8
11	Ultralow-Loss SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 1954-1960	2.9	23
10	Evaluation of the quality of commercial silicon carbide wafers by an optical non-destructive inspection technique. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 988-992	1.6	5
9	Impact ionization coefficients of 4H silicon carbide. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 1380-1382	3.4	95
8	Parameters required to simulate electric characteristics of SiC devices for n-type 4H-SiC. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 5601-5606	2.5	57
7	Dependence of acceptor levels and hole mobility on acceptor density and temperature in Al-doped p-type 4H-SiC epilayers. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 2708-2715	2.5	69
6	Transport properties of two-dimensional electron gas in a strained-Si/SiGe heterostructure at low carrier densities. <i>Thin Solid Films</i> , <b>2000</b> , 369, 328-332	2.2	
5	Mobility modulation of two-dimensional hole gas in a p-type Si/SiGe modulation doped heterostructure by back-gating. <i>Semiconductor Science and Technology</i> , <b>1998</b> , 13, 1477-1479	1.8	7
4	Theoretical prediction on the formation of icosahedra in quasicrystals. <i>Solid State Communications</i> , <b>1992</b> , 84, 227-229	1.6	3

3	Localization in hybridized Fibonacci quasi- crystals. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1992</b> , 14, L5-L9	3.1	1
2	Fractal Nature of the Electronic Structure of a Penrose Tiling Lattice in a Magnetic Field. <i>Journal of the Physical Society of Japan</i> , <b>1989</b> , 58, 260-268	1.5	10
1	Electronic properties of a Penrose tiling lattice in a magnetic field. <i>Solid State Communications</i> , <b>1987</b> , 62, 79-83	1.6	20